

# BC807K-Q series

# 45 V, 500 mA PNP general-purpose transistors

Rev. 1 — 15 July 2025

**Product data sheet** 

### 1. General description

PNP general-purpose transistors in a small SOT23 Surface-Mounted Device (SMD) plastic package.

**Table 1. Product overview** 

Type number	Package		NPN complement
	Nexperia	JEDEC	
BC807K-16-Q	SOT23	-	BC817K-16-Q
BC807K-25-Q			BC817K-25-Q
BC807K-40-Q			BC817K-40-Q

### 2. Features and benefits

- Three current gain selections
- High power dissipation capability
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

· General-purpose switching and amplification

#### 4. Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	-	-45	V
I <sub>C</sub>	collector current	T <sub>amb</sub> = 25 °C		-	-	-500	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms; T <sub>amb</sub> = 25 °C		-	-	-1	А
h <sub>FE</sub>	DC current gain						
	BC807K-16-Q	V <sub>CE</sub> = -1 V; I <sub>C</sub> = -100 mA T <sub>amb</sub> = 25 °C	[1]	100	-	250	
	BC807K-25-Q		[1]	160	-	400	
	BC807K-40-Q		[1]	250	-	600	

[1] pulsed;  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ 



# 5. Pinning information

#### **Table 3. Pinning**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	Е	emitter		В
3	С	collector		
				Ë sym132
			1 2	5,111.52

# 6. Ordering information

#### **Table 4. Ordering information**

Type number	Package	Package						
	Name	Description	Version					
BC807K-16-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch;	SOT23					
BC807K-25-Q		2.9 mm x 1.3 mm x 1 mm body						
BC807K-40-Q								

# 7. Marking

#### Table 5. Marking

Type number	Marking code[1]
BC807K-16-Q	HA%
BC807K-25-Q	HB%
BC807K-40-Q	HC%

[1] % = placeholder for manufacturing site code

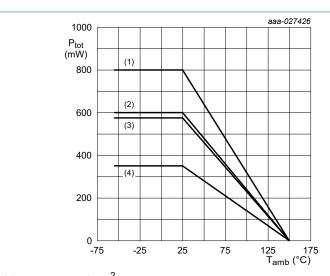
### 8. Limiting values

#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	open emitter		-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current				-500	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	single pulse; t <sub>p</sub> ≤ 1 ms		-1	А
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	350	mW
			[2]	-	575	mW
			[3]	-	600	mW
			[4]	-	800	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB; single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB; 4-layer copper; tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB; 4-layer copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB, 4-layer copper; 1 cm<sup>2</sup>
- (2) FR4 PCB, 4-layer copper; standard footprint
- (3) FR4 PCB, single-sided copper; 1 cm<sup>2</sup>
- (4) FR4 PCB, single-sided copper; standard footprint

Fig. 1. Power derating curves

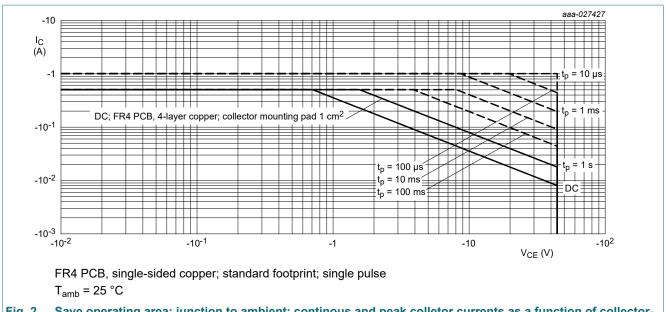


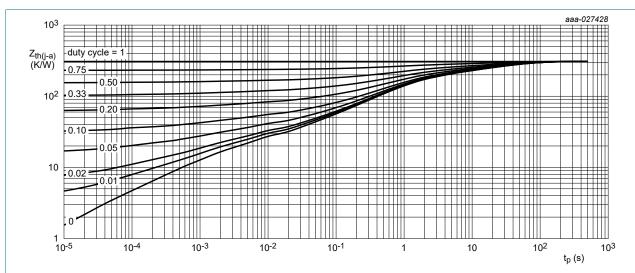
Fig. 2. Save operating area; junction to ambient; continous and peak colletor currents as a function of collectoremitter voltage

### 9. Thermal characteristics

**Table 7. Thermal characteristics** 

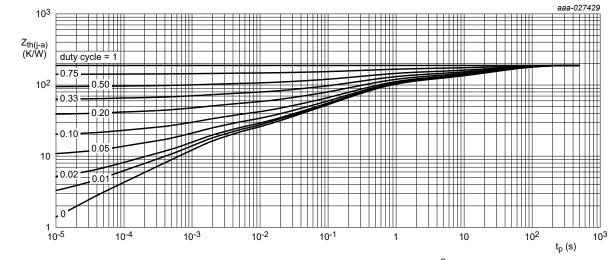
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	358	K/W
			[2]	-	-	218	K/W
			[3]	-	-	209	K/W
			[4]	-	-	157	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	60	K/W

- [1] Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB; 4-layer copper; tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB; 4-layer copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.



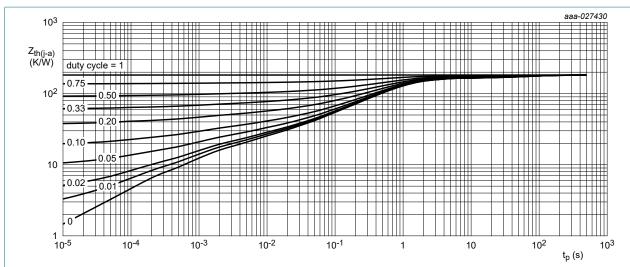
FR4 PCB, single-sided, tin-plated and standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



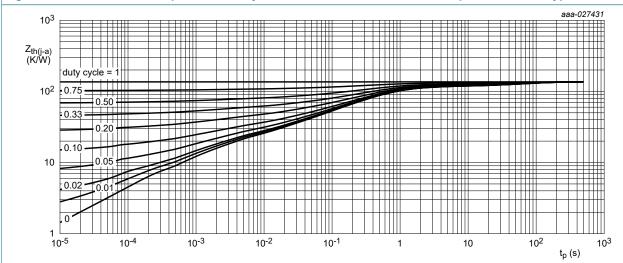
FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin plated and standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin plated; mounting pad for collector 1 cm<sup>2</sup>

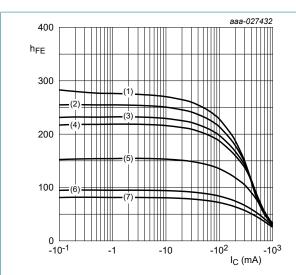
Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 10. Characteristics

#### **Table 8. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		-50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C$ = -10 mA; $I_B$ = 0 A; $T_{amb}$ = 25 °C		-45	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage	$I_E = -100 \ \mu A; I_C = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		-5	-	-	V
I <sub>CBO</sub>	collector-base	V <sub>CB</sub> = -25 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
	cut-off current	V <sub>CB</sub> = -25 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain						
	BC807K-16-Q	V <sub>CE</sub> = -1 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	[1]	100	-	250	
	BC807K-25-Q		[1]	160	-	400	
BC807K-40	BC807K-40-Q		[1]	250	-	600	
	BC807K-16-Q BC807K-25-Q BC807K-40-Q	V <sub>CE</sub> = -1 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	[1]	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C	[1]	-	-	-700	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	-1.2	V
V <sub>BE</sub>	base-emitter voltage	V <sub>CE</sub> = -1 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	[1]	-	-	-1.2	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C		80	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	7	-	pF
C <sub>e</sub>	emitter capacitance						
	BC807K-16-Q	$V_{EB} = -0.5 \text{ V}; I_C = I_c = 0 \text{ A}; f = 1 \text{ MHz};$		-	50	-	pF
	BC807K-25-Q	T <sub>amb</sub> = 25 °C		-	45	-	pF
	BC807K-40-Q			-	37	-	pF

<sup>[1]</sup> pulsed;  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ 



$$V_{CE} = -1 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 125 \, ^{\circ}C$$

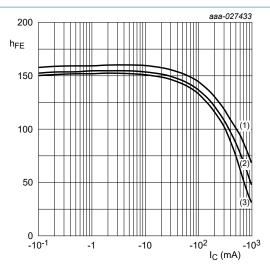
(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

(4) 
$$T_{amb}$$
 = 85 °C

(5) 
$$T_{amb} = 25 \, ^{\circ}C$$

(6) 
$$T_{amb}$$
 = -40 °C

(7) 
$$T_{amb} = -55 \, ^{\circ}C$$

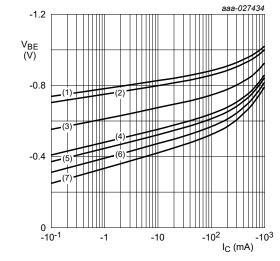


(1) 
$$V_{CE} = -5 V$$

(3) 
$$V_{CE} = -1 V$$

Fig. 8. BC807K-16-Q: DC current gain as a function of collector current; typical values





$$V_{CE} = -1 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

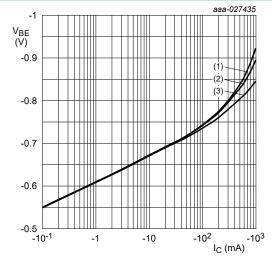
(2) 
$$T_{amb} = -40 \, ^{\circ}C$$

(3) 
$$T_{amb} = 25 \, ^{\circ}C$$

(6) 
$$T_{amb} = 125 \, ^{\circ}C$$

$$(7) T_{amb} = 150 °C$$

Fig. 9. BC807K-16-Q: Base-emitter voltage as a function of collector current; typical values

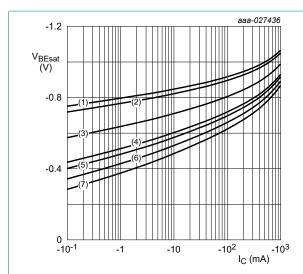


(1) 
$$V_{CE} = -1 V$$

$$(2) V_{CE} = -2 V$$

(3) 
$$V_{CE} = -5 V$$

Fig. 10. BC807K-16-Q: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = -40 \, ^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

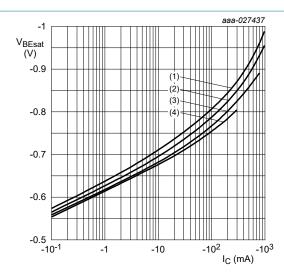
(4)  $T_{amb}$  = 85 °C

(5)  $T_{amb} = 100 \, ^{\circ}C$ 

(6) T<sub>amb</sub> = 125 °C

 $(7) T_{amb} = 150 °C$ 

Fig. 11. BC807K-16-Q: Base-emitter voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

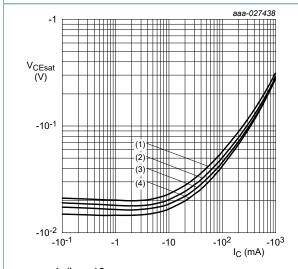
(1)  $I_C/I_B = 10$ 

(2)  $I_C/I_B = 20$ 

(3)  $I_C/I_B = 50$ 

 $(4) I_C/I_B = 100$ 

Fig. 12. BC807K-16-Q: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=10$ 

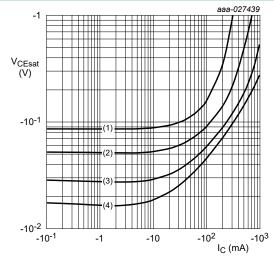
(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 85 \, ^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 13. BC807K-16-Q: Collector-emitter saturation voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

(1)  $I_C/I_B = 100$ 

(2)  $I_C/I_B = 50$ 

(3)  $I_C/I_B = 20$ 

(4)  $I_C/I_B = 10$ 

Fig. 14. BC807K-16-Q: Collector-emitter saturation voltage as a function of collector current; typical values

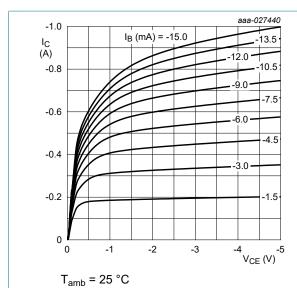
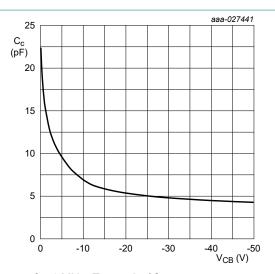


Fig. 15. BC807K-16-Q: Collector current as a function of Fig. 16. BC807K-16-Q: Collector capacitance as a collector-emitter voltage; typical values



f = 1 MHz; T<sub>amb</sub> = 25 °C

function of collector-base voltage; typical values

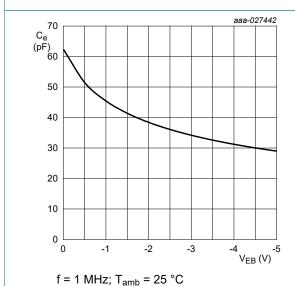
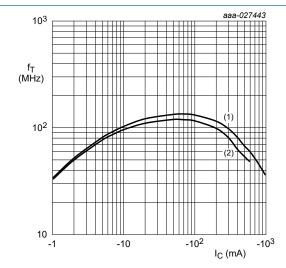


Fig. 17. BC807K-16-Q: Emitter capacitance as a function of emitter-base voltage; typical values

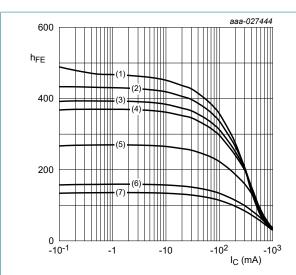


f = 100 MHz;  $T_{amb} = 25 \text{ °C}$ 

(1)  $V_{CE} = -5 V$ 

(2)  $V_{CE} = -1 V$ 

Fig. 18. BC807K-16-Q: Transition frequency as a function of collector current; typical values



$$V_{CE} = -1 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 125 \, ^{\circ}C$$

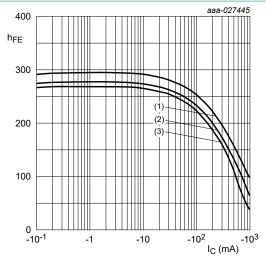
(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

(4) 
$$T_{amb} = 85 \, ^{\circ}C$$

(5) 
$$T_{amb} = 25 \, ^{\circ}C$$

(6) 
$$T_{amb} = -40 \, ^{\circ}C$$

$$(7) T_{amb} = -55 °C$$



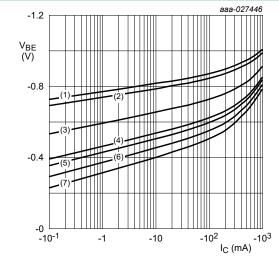
(1) 
$$V_{CE} = -5 V$$

(2) 
$$V_{CE} = -2 V$$

(3) 
$$V_{CE} = -1 V$$

Fig. 20. BC807K-25-Q: DC current gain as a function of collector current; typical values





$$V_{CE} = -1 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

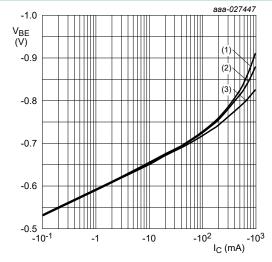
(2) 
$$T_{amb} = -40 \, ^{\circ}C$$

(3) 
$$T_{amb} = 25 \, ^{\circ}C$$

(6) 
$$T_{amb} = 125 \, ^{\circ}C$$

$$(7) T_{amb} = 150 °C$$

Fig. 21. BC807K-25-Q: Base-emitter voltage as a function of collector current; typical values

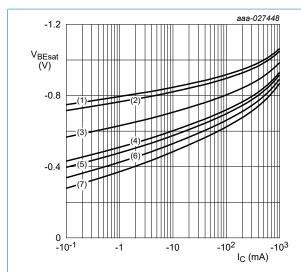


(1) 
$$V_{CE} = -1 V$$

$$(2) V_{CE} = -2 V$$

$$(3) V_{CE} = -5 V$$

Fig. 22. BC807K-25-Q: Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = -40 \, ^{\circ}C$$

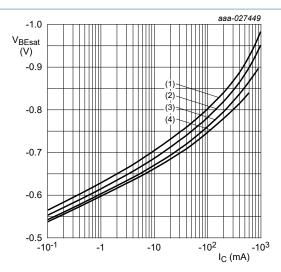
(3) 
$$T_{amb} = 25 \, ^{\circ}C$$

(4) 
$$T_{amb} = 85 \, ^{\circ}C$$

$$(5) T_{amb} = 100 °C$$

(7) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 23. BC807K-25-Q: Base-emitter voltage as a function of collector current; typical values



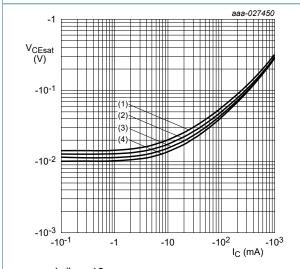
(1) 
$$I_C/I_B = 10$$

(2) 
$$I_C/I_B = 20$$

(3) 
$$I_C/I_B = 50$$

$$(4) I_C/I_B = 100$$

Fig. 24. BC807K-25-Q: Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=10$$

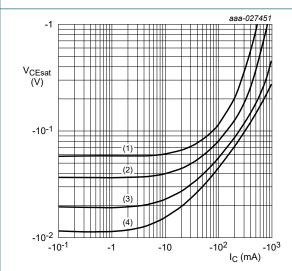
(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 85 °C

(3) 
$$T_{amb} = 25 \, ^{\circ}C$$

(4) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 25. BC807K-25-Q: Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 20$$

(4) 
$$I_C/I_B = 10$$

Fig. 26. BC807K-25-Q: Collector-emitter saturation voltage as a function of collector current; typical values

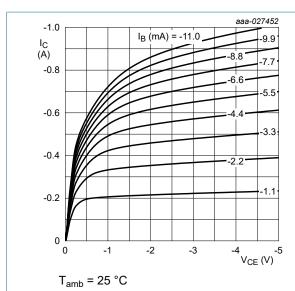
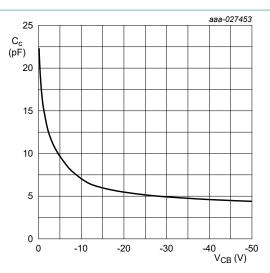


Fig. 27. BC807K-25-Q: Collector current as a function of Fig. 28. BC807K-25-Q: Collector capacitance as a collector-emitter voltage; typical values



f = 1 MHz; T<sub>amb</sub> = 25 °C

function of collector-base voltage; typical values

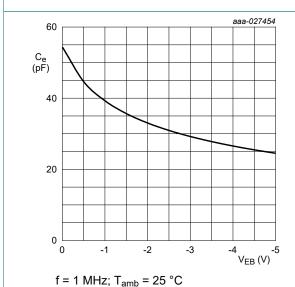
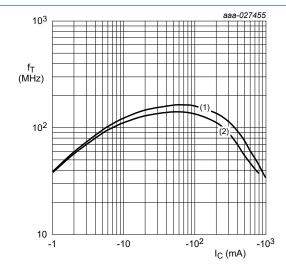


Fig. 29. BC807K-25-Q: Emitter capacitance as a function of emitter-base voltage; typical values

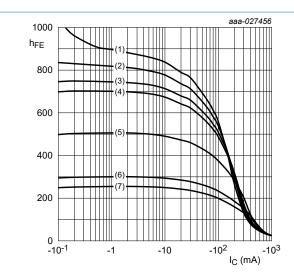


f = 100 MHz;  $T_{amb} = 25 \text{ °C}$ 

(1)  $V_{CE} = -5 V$ 

(2)  $V_{CE} = -1 V$ 

Fig. 30. BC807K-25-Q: Transition frequency as a function of collector current; typical values



 $V_{CE} = -1 V$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 125 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

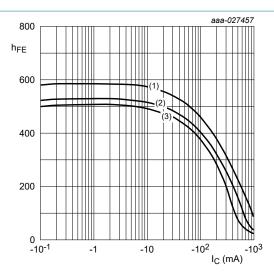
(4) T<sub>amb</sub> = 85 °C

(5)  $T_{amb} = 25 \, ^{\circ}C$ 

(6)  $T_{amb} = -40 \, ^{\circ}C$ 

 $(7) T_{amb} = -55 °C$ 





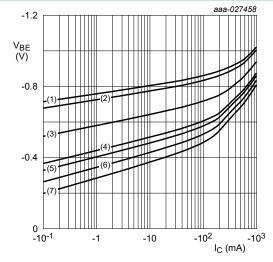
 $T_{amb} = 25 \, ^{\circ}C$ 

(1)  $V_{CE} = -5 V$ 

(2)  $V_{CE} = -2 V$ 

(3)  $V_{CE} = -1 V$ 

Fig. 32. BC807K-40-Q: DC current gain as a function of collector current; typical values



 $V_{CE} = -1 V$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = -40 \, ^{\circ}C$ 

(3) T<sub>amb</sub> = 25 °C

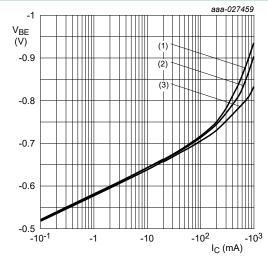
(4) T<sub>amb</sub> = 85 °C

 $(5) T_{amb} = 100 °C$ 

(6)  $T_{amb} = 125 \, ^{\circ}C$ 

(7)  $T_{amb}$  = 150 °C

Fig. 33. BC807K-40-Q: Base-emitter voltage as a function of collector current; typical values



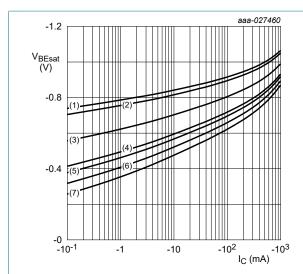
 $T_{amb} = 25 \, ^{\circ}C$ 

(1)  $V_{CE} = -1 V$ 

(2)  $V_{CE} = -2 V$ 

(3)  $V_{CE} = -5 V$ 

Fig. 34. BC807K-40-Q: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = -40 \, ^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

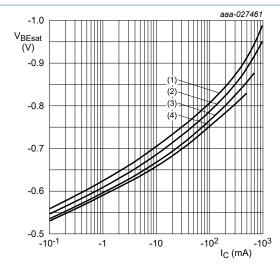
(4)  $T_{amb} = 85 \, ^{\circ}C$ 

(5)  $T_{amb} = 100 \, ^{\circ}C$ 

(6)  $T_{amb} = 125 \, ^{\circ}C$ 

 $(7) T_{amb} = 150 °C$ 

Fig. 35. BC807K-40-Q: Base-emitter voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

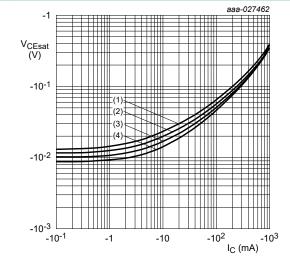
(1)  $I_C/I_B = 10$ 

(2)  $I_C/I_B = 20$ 

(3)  $I_C/I_B = 50$ 

 $(4) I_C/I_B = 100$ 

Fig. 36. BC807K-40-Q: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

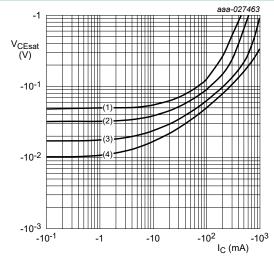
(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 85 \, ^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 37. BC807K-40-Q: Collector-emitter saturation voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

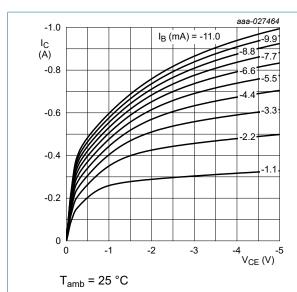
(1)  $I_C/I_B = 100$ 

(2)  $I_{\rm C}/I_{\rm B} = 50$ 

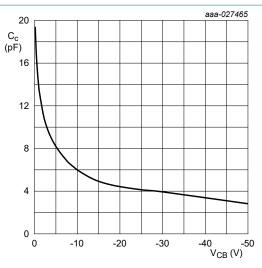
(3)  $I_C/I_B = 20$ 

(4)  $I_C/I_B = 10$ 

Fig. 38. BC807K-40-Q: Collector-emitter saturation voltage as a function of collector current; typical values



collector-emitter voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$ 

Fig. 39. BC807K-40-Q: Collector current as a function of Fig. 40. BC807K-40-Q: Collector capacitance as a function of collector-base voltage; typical values

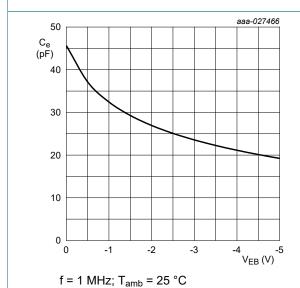
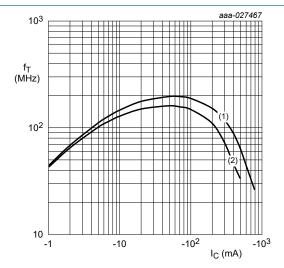


Fig. 41. BC807K-40-Q: Emitter capacitance as a function of emitter-base voltage; typical values



f = 100 MHz;  $T_{amb} = 25 \text{ °C}$ 

(1)  $V_{CE} = -5 \text{ V}$ 

(2)  $V_{CE} = -1 V$ 

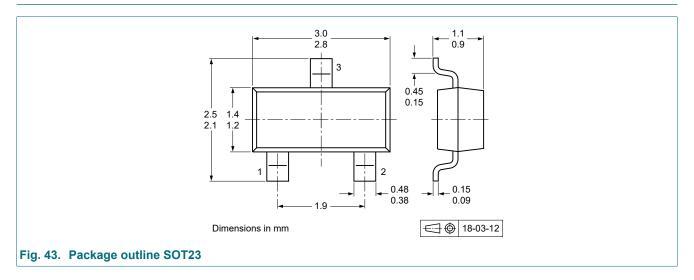
Fig. 42. BC807K-40-Q: Transition frequency as a function of collector current; typical values

#### 11. Test information

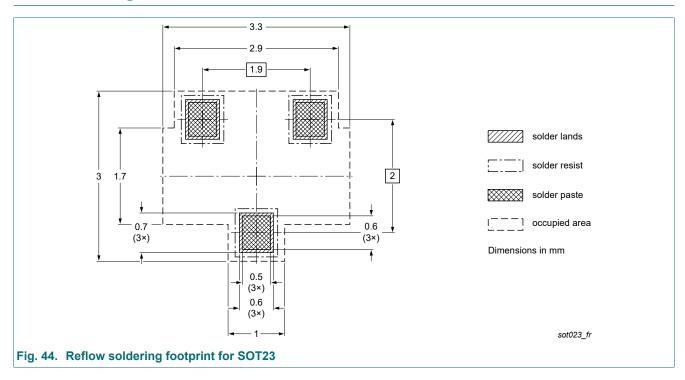
### 11.1. Quality information

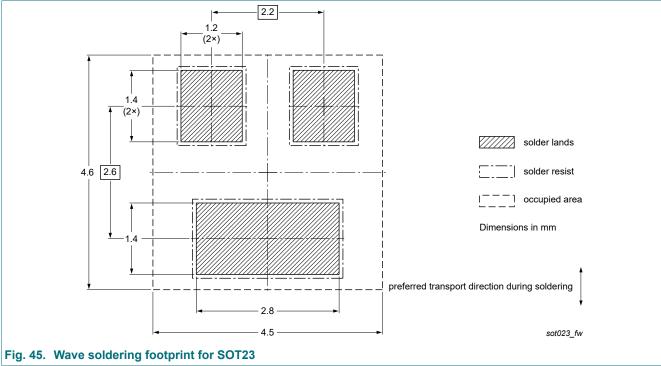
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



# 13. Soldering





# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC807K-Q_SER v.1	20250715	Product data sheet	-	-

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 15 July 2025

Rev. 1 — 15 July 2025

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